THE DATASHEET OF

BSS138LT1

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MOSFET – Power, N-Channel, SOT-23
200 mA, 50 V

BSS138L, BVSS138L

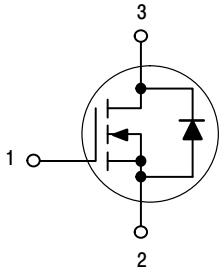
200 mA, 50 V
$R_{DS(on)}$ = 3.5 Ω

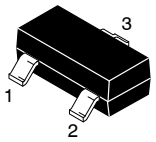
Typical applications are DC−DC converters, power management in portable and battery−powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low Threshold Voltage ($V_{GS(th)}$: 0.85 V−1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT−23 Surface Mount Package Saves Board Space
- HBM Class 0A, MM Class M1A, CDM Class IV (Note 3)
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

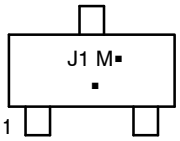
N−Channel





SOT−23
CASE 318
STYLE 21

MARKING DIAGRAM



J1 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage	V_{DSS}	50	Vdc
Gate−to−Source Voltage − Continuous	V_{GS}	± 20	Vdc
Drain Current − Continuous @ T_A = 25°C − Pulsed Drain Current ($t_p \le 10$ μs)	 I_D I_{DM}	 200 800	mA
Total Power Dissipation @ T_A = 25°C	P_D	225	mW
Operating and Storage Temperature Range	T_J, T_{stg}	− 55 to 150	°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

Device	Package	Shipping†
BSS138LT1G, BVSS138LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BSS138LT7G	SOT−23 (Pb−Free)	3,500 / Tape & Reel
BSS138LT3G, BVSS138LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 250 μAdc)		$V_{(BR)DSS}$	50	–	–	Vdc
Zero Gate Voltage Drain Current		I_{DSS}				μAdc
(V_{DS} = 25 Vdc, V_{GS} = 0 Vdc, 25°C)			–	–	0.1	
(V_{DS} = 50 Vdc, V_{GS} = 0 Vdc, 25°C)			–	–	0.5	
(V_{DS} = 50 Vdc, V_{GS} = 0 Vdc, 150°C)			–	–	5.0	
Gate−Source Leakage Current (V_{GS} = ± 20 Vdc, V_{DS} = 0 Vdc)		I_{GSS}	–	–	±0.1	μAdc
ON CHARACTERISTICS (Note 1)						
Gate−Source Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.0 mAdc)		$V_{GS(th)}$	0.85	–	1.5	Vdc
Static Drain−to−Source On−Resistance		$r_{DS(on)}$				Ω
(V_{GS} = 2.75 Vdc, I_D < 200 mAdc, T_A = −40°C to +85°C)			–	5.6	10	
(V_{GS} = 5.0 Vdc, I_D = 200 mAdc)			–	–	3.5	
Forward Transconductance (V_{DS} = 25 Vdc, I_D = 200 mAdc, f = 1.0 kHz)		g_{fs}	100	–	–	mmhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 25 Vdc, V_{GS} = 0, f = 1 MHz)	C_{iss}	–	40	50	pF
Output Capacitance	(V_{DS} = 25 Vdc, V_{GS} = 0, f = 1 MHz)	C_{oss}	–	12	25	
Transfer Capacitance	(V_{DG} = 25 Vdc, V_{GS} = 0, f = 1 MHz)	C_{rss}	–	3.5	5.0	
SWITCHING CHARACTERISTICS (Note 2)						
Turn−On Delay Time	(V_{DD} = 30 Vdc, I_D = 0.2 Adc,)	$t_{d(on)}$	–	–	20	ns
Turn−Off Delay Time		$t_{d(off)}$	–	–	20	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.
3. ESD between the gate and source serves only, no gate overvoltage rating is implied.

TYPICAL ELECTRICAL CHARACTERISTICS

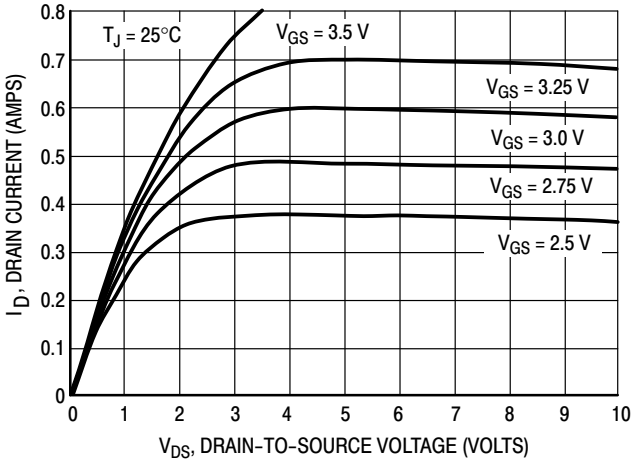


Figure 1. On−Region Characteristics

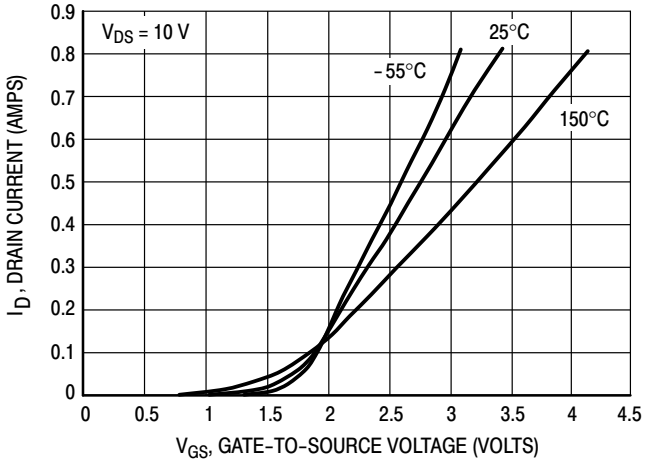


Figure 2. Transfer Characteristics

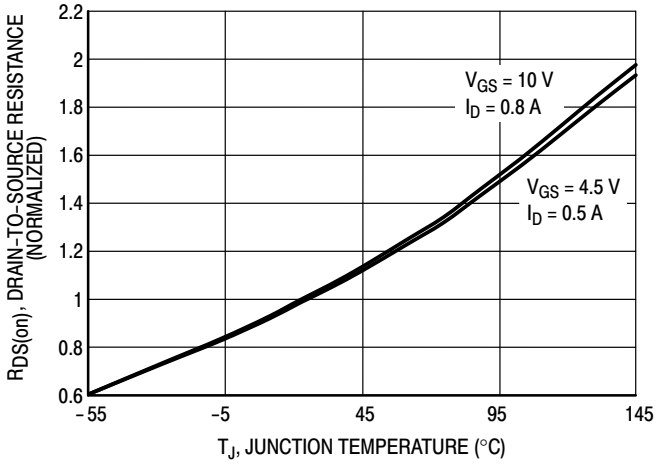


Figure 3. On−Resistance Variation with Temperature

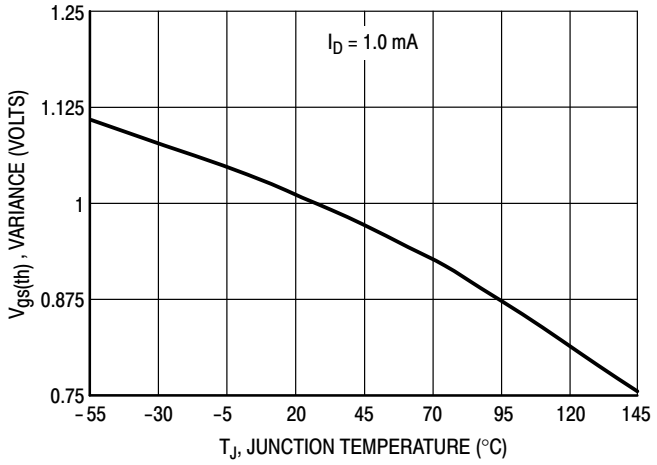


Figure 4. Threshold Voltage Variation with Temperature

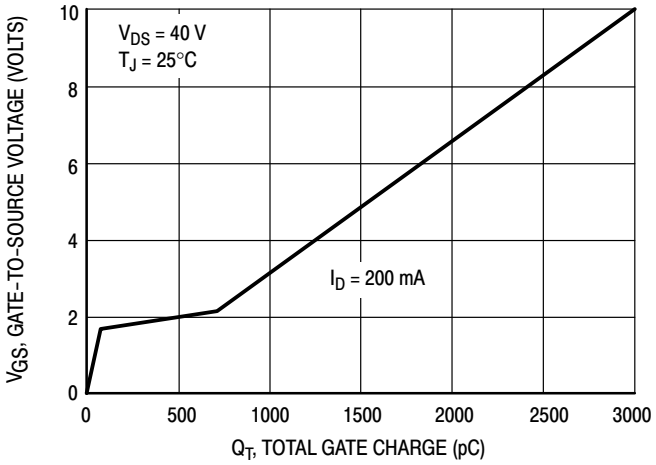


Figure 5. Gate Charge

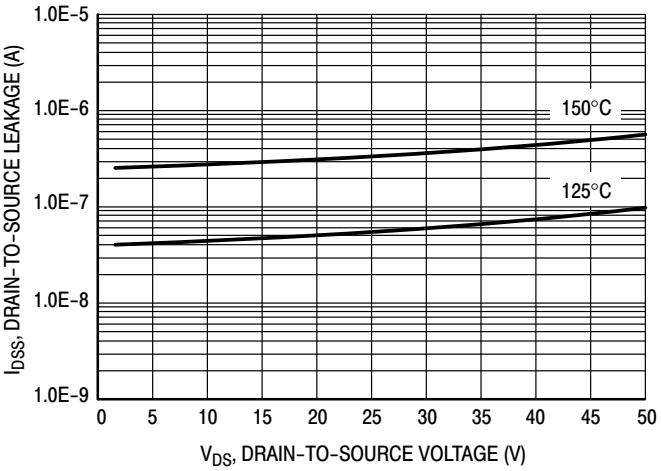


Figure 6. IDSS

TYPICAL ELECTRICAL CHARACTERISTICS

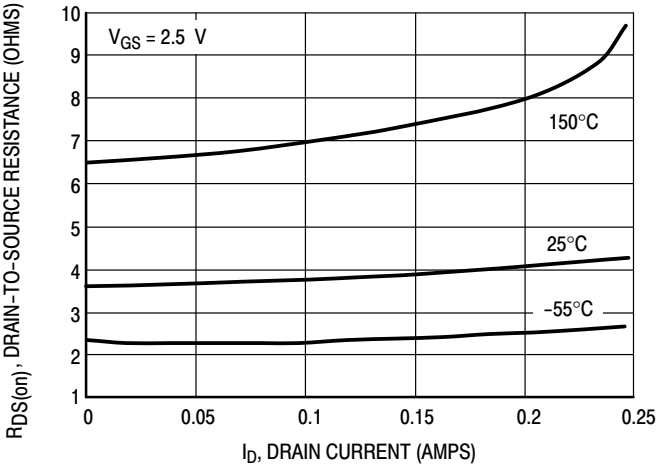


Figure 7. On−Resistance versus Drain Current

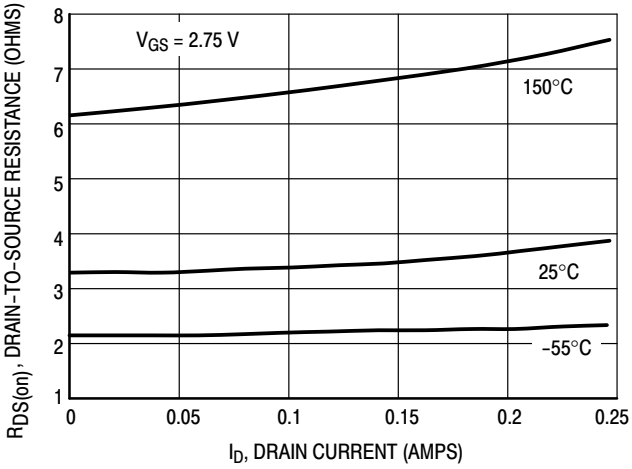


Figure 8. On−Resistance versus Drain Current

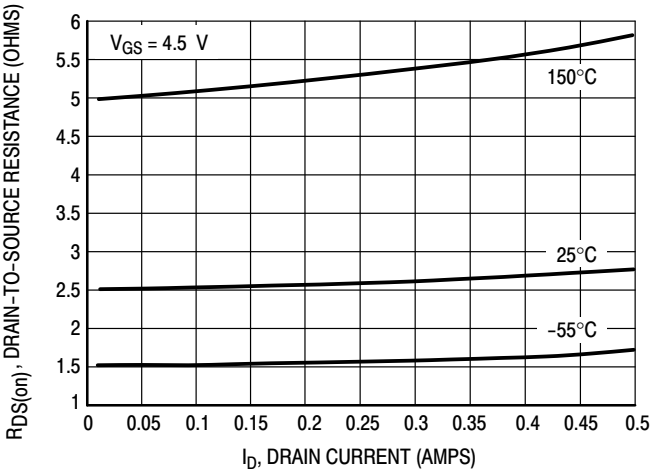


Figure 9. On−Resistance versus Drain Current

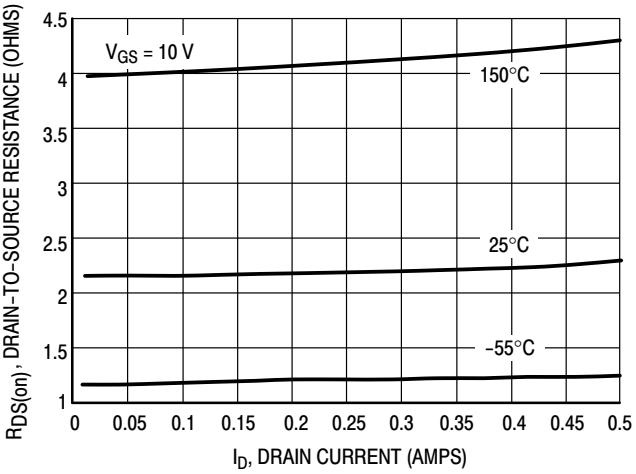


Figure 10. On−Resistance versus Drain Current

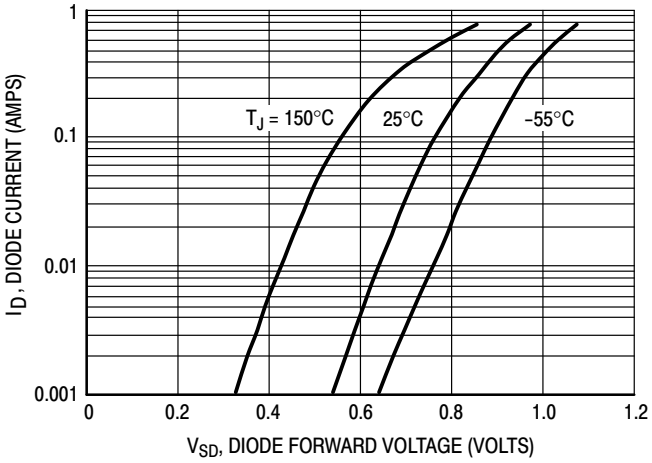


Figure 11. Body Diode Forward Voltage

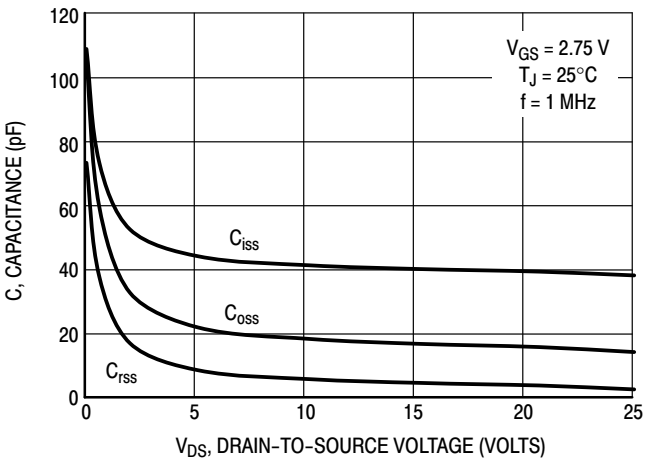


Figure 12. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

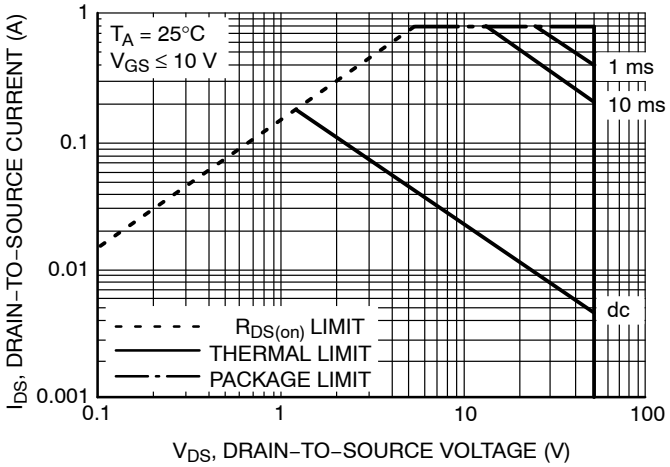
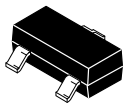


Figure 13. Safe Operating Area

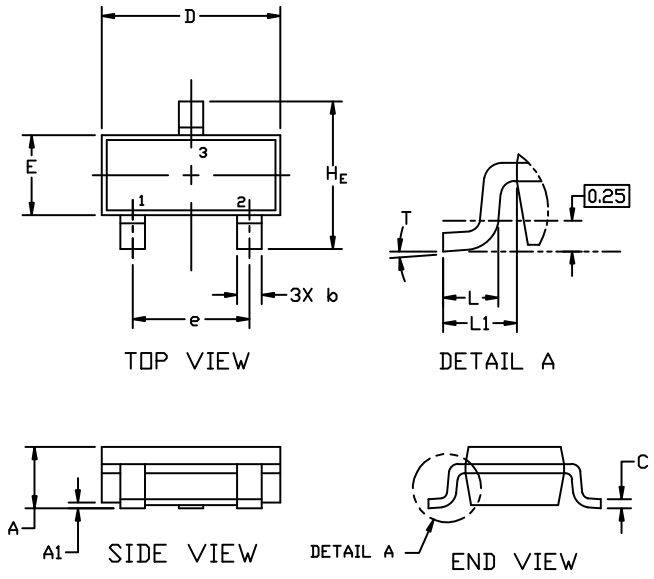
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 4:1

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

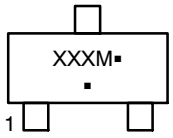


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

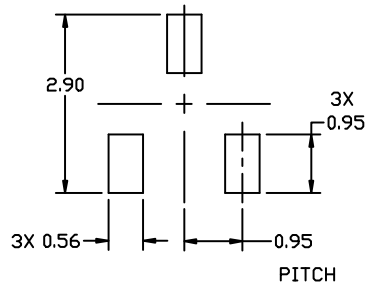
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOT−23 (TO−236)**		**PAGE 1 OF 2**

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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